## 2N5088, 2N5089

## Amplifier Transistors

NPN Silicon

## Features

- $\mathrm{Pb}-$ Free Packages are Available*


## MAXIMUM RATINGS

\begin{tabular}{|c|c|c|c|}
\hline Rating \& Symbol \& Value \& Unit <br>
\hline $\begin{array}{lr}\text { Collector - Emitter Voltage } \\ & \\ \\ \\ \text { 2N5088 } \\ \text { 2N5089 }\end{array}$ \& $\mathrm{V}_{\text {CEO }}$ \& $$
\begin{aligned}
& 30 \\
& 25
\end{aligned}
$$ \& Vdc <br>
\hline Collector - Base Voltage

2N5088

2N5089 \& $\mathrm{V}_{\text {CBO }}$ \& $$
\begin{aligned}
& 35 \\
& 30
\end{aligned}
$$ \& Vdc <br>

\hline Emitter - Base Voltage \& $\mathrm{V}_{\text {Ebo }}$ \& 3.0 \& Vdc <br>
\hline Collector Current - Continuous \& $I_{C}$ \& 50 \& mAdc <br>

\hline Total Device Dissipation @ $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ Derate above $25^{\circ} \mathrm{C}$ \& $\mathrm{P}_{\mathrm{D}}$ \& \[
$$
\begin{aligned}
& 625 \\
& 5.0
\end{aligned}
$$

\] \& \[

\underset{\mathrm{mW} /{ }^{\circ} \mathrm{C}}{\mathrm{~m}}
\] <br>

\hline Total Device Dissipation @ $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ Derate above $25^{\circ} \mathrm{C}$ \& $\mathrm{P}_{\mathrm{D}}$ \& \[
$$
\begin{aligned}
& 1.5 \\
& 12
\end{aligned}
$$

\] \& \[

$$
\begin{gathered}
\mathrm{W} \\
\mathrm{~mW} /{ }^{\circ} \mathrm{C}
\end{gathered}
$$
\] <br>

\hline Operating and Storage Junction Temperature Range \& $\mathrm{T}_{\mathrm{J}}, \mathrm{T}_{\text {stg }}$ \& -55 to +150 \& ${ }^{\circ} \mathrm{C}$ <br>
\hline
\end{tabular}

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
| :--- | :---: | :---: | :---: |
| Thermal Resistance, Junction-to-Ambient <br> (Note 1) | $\mathrm{R}_{\theta \mathrm{JA}}$ | 200 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Thermal Resistance, Junction-to-Case | $\mathrm{R}_{\theta \mathrm{JC}}$ | 83.3 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the
Recommended Operating Conditions may affect device reliability.

1. $R_{\theta J A}$ is measured with the device soldered into a typical printed circuit board
*For additional information on our $\mathrm{Pb}-F r e e$ strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor ${ }^{\circledR}$
http://onsemi.com


ORDERING INFORMATION

| Device | Package | Shipping ${ }^{\dagger}$ |
| :--- | :---: | :---: |
| 2N5088G | TO-92 <br> (Pb-Free) | 5000 Units/Bulk |
| 2N2088RLRAG | TO-92 <br> (Pb-Free) | 2000/Tape \& Reel |
| 2N5089G | TO-92 <br> (Pb-Free) | 5000 Units/Bulk |
| 2N2089RLRE | TO-92 | 2000/Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS $\left(T_{A}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)

| Characteristic |  | Symbol | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS |  |  |  |  |  |
| $\begin{aligned} & \text { Collector-Emitter Breakdown Voltage (Note 2) } \\ & \quad\left(I_{C}=1.0 \mathrm{mAdc}, \mathrm{I}_{\mathrm{B}}=0\right) \end{aligned}$ | $\begin{aligned} & \text { 2N5088 } \\ & \text { 2N5089 } \end{aligned}$ | $\mathrm{V}_{\text {(BR) }}$ CEO | $\begin{aligned} & 30 \\ & 25 \end{aligned}$ | - | Vdc |
| Collector-Base Breakdown Voltage $\left(\mathrm{I}_{\mathrm{C}}=100 \mu \mathrm{Adc}, \mathrm{I}_{\mathrm{E}}=0\right)$ | $\begin{aligned} & \text { 2N5088 } \\ & \text { 2N5089 } \end{aligned}$ | $\mathrm{V}_{\text {(BR) }}$ CBO | $\begin{aligned} & 35 \\ & 30 \end{aligned}$ | - | Vdc |
| $\begin{gathered} \text { Collector Cutoff Current } \\ \left(V_{C B}=20 \mathrm{Vdc}, I_{E}=0\right) \\ \left(V_{C B}=15 \mathrm{Vdc}, I_{E}=0\right) \end{gathered}$ | $\begin{aligned} & \text { 2N5088 } \\ & \text { 2N5089 } \end{aligned}$ | $\mathrm{I}_{\text {cbo }}$ | - | $\begin{aligned} & 50 \\ & 50 \end{aligned}$ | nAdc |
| Emitter Cutoff Current $\left(\mathrm{V}_{\mathrm{EB}(\text { off })}=3.0 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=0\right)$ $\left(\mathrm{V}_{\mathrm{EB}}\right.$ (off) $\left.=4.5 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=0\right)$ $\left(\mathrm{V}_{\mathrm{EB}(\text { off })}=4.5 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=0\right)$ |  | $\mathrm{l}_{\text {ebo }}$ | - | $\begin{gathered} 50 \\ 100 \end{gathered}$ | nAdc |

## ON CHARACTERISTICS

| $\begin{aligned} & \text { DC Current Gain } \\ & \text { (IC } \left.=100 \mu \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}\right) \\ & \left(\mathrm{I}_{\mathrm{C}}=1.0 \mathrm{mAdc}, \mathrm{~V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}\right) \\ & \left(\mathrm{I}_{\mathrm{C}}=10 \mathrm{mAdc}, \mathrm{~V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}\right)(\text { Note } 2) \end{aligned}$ | 2N5088 2N5089 2N5088 2N5089 2N5088 2N5089 | $\mathrm{h}_{\text {FE }}$ | $\begin{aligned} & 300 \\ & 400 \\ & \\ & 350 \\ & 450 \\ & 300 \\ & 400 \end{aligned}$ | $\begin{gathered} 900 \\ 1200 \\ - \\ - \end{gathered}$ | - |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Collector-Emitter Saturation Voltage $\left(I_{C}=10 \mathrm{mAdc}, \mathrm{I}_{\mathrm{B}}=1.0 \mathrm{mAdc}\right)$ |  | $\mathrm{V}_{\mathrm{CE} \text { (sat) }}$ | - | 0.5 | Vdc |
| Base-Emitter On Voltage $\left(\mathrm{I}_{\mathrm{C}}=10 \mathrm{mAdc}, \mathrm{V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}\right)($ Note 2) |  | $V_{B E(\text { (on })}$ | - | 0.8 | Vdc |

SMALL-SIGNAL CHARACTERISTICS

| $\begin{aligned} & \text { Current-Gain - Bandwidth Product } \\ & \quad\left(\mathrm{I}_{\mathrm{C}}=500 \mu \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}, \mathrm{f}=20 \mathrm{MHz}\right) \end{aligned}$ |  | $\mathrm{f}_{\mathrm{T}}$ | 50 | - | MHz |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Collector-Base Capacitance $\left(\mathrm{V}_{\mathrm{CB}}=5.0 \mathrm{Vdc}, \mathrm{I}_{\mathrm{E}}=0, \mathrm{f}=1.0 \mathrm{MHz}\right)$ |  | $\mathrm{C}_{\mathrm{cb}}$ | - | 4.0 | pF |
| Emitter-Base Capacitance $\left(\mathrm{V}_{\mathrm{EB}}=0.5 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=0, \mathrm{f}=1.0 \mathrm{MHz}\right)$ |  | $\mathrm{C}_{\text {eb }}$ | - | 10 | pF |
| Small-Signal Current Gain $\left(\mathrm{I}_{\mathrm{C}}=1.0 \mathrm{mAdc}, \mathrm{V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}, \mathrm{f}=1.0 \mathrm{kHz}\right)$ | $\begin{aligned} & \text { 2N5088 } \\ & \text { 2N5089 } \end{aligned}$ | $\mathrm{hfe}_{\text {fe }}$ | $\begin{aligned} & 350 \\ & 450 \end{aligned}$ | $\begin{aligned} & 1400 \\ & 1800 \end{aligned}$ | - |
| Noise Figure $\left(\mathrm{I}_{\mathrm{C}}=100 \mu \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}, \mathrm{R}_{\mathrm{S}}=1.0 \mathrm{k} \Omega, \mathrm{f}=1.0 \mathrm{kHz}\right)$ | $\begin{aligned} & \text { 2N5088 } \\ & \text { 2N5089 } \end{aligned}$ | NF | - | $\begin{aligned} & 3.0 \\ & 2.0 \end{aligned}$ | dB |

2. Pulse Test: Pulse Width $\leq 300 \mu \mathrm{~s}$, Duty Cycle $\leq 2.0 \%$.


Figure 1. Transistor Noise Model

## 2N5088, 2N5089

## NOISE CHARACTERISTICS

$\left(\mathrm{V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}, \mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}\right.$ )
NOISE VOLTAGE


Figure 2. Effects of Frequency


Figure 4. Noise Current


Figure 3. Effects of Collector Current


Figure 5. Wideband Noise Figure

100 Hz NOISE DATA


Figure 6. Total Noise Voltage


Figure 7. Noise Figure


Figure 8. DC Current Gain


Figure 9. "On" Voltages


Figure 11. Capacitance


Figure 10. Temperature Coefficients


Figure 12. Current-Gain - Bandwidth Product


STRAIGHT LEAD


BENT LEAD


STRAIGHT LEAD


BENT LEAD


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. CONTOUR OF PACKAGE BEYOND DIMENSION RIS CONTOUR OF PACKA
4. DIMENSION F APPLIES BETWEEN DIMENSIONS $P$ AND L. DIMENSIONS D AND J APPLY BETWEEN DIMENSIONS L AND K MINIMUM. THE LEAD
DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIIUM.

|  | INCHES |  | MILLIMETERS |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
|  | 0.175 | 0.205 | 4.44 | 5.21 |
| B | 0.290 | 0.310 | 7.37 | 7.87 |
| C | 0.125 | 0.165 | 3.18 | 4.19 |
| D | 0.018 | 0.021 | 0.46 | 0.53 |
| F | 0.016 | 0.019 | 0.41 | 0.48 |
| G | 0.045 | 0.055 | 1.15 | 1.39 |
| H | 0.095 | 0.05 | 2.42 | 2.66 |
| J | 0.018 | 0.024 | 0.46 | 0.61 |
| K | 0.500 | --- | 12.70 | --- |
| L | 0.250 | --- | 6.35 | --- |
| N | 0.080 | 0.105 | 2.04 | 2.66 |
| P | --- | 0.100 | -- | 2.54 |
| R | 0.135 | --- | 3.43 | --- |
| V | 0.135 | --- | 3.43 | --- |

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION FAPPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN DIMENSIONS LAND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

| DIM | INCHES |  | MILLIMETERS |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
| A | 0.175 | 0.205 | 4.44 | 5.21 |
| B | 0.290 | 0.310 | 7.37 | 7.87 |
| C | 0.125 | 0.165 | 3.18 | 4.19 |
| D | 0.018 | 0.021 | 0.46 | 0.53 |
| G | 0.094 | 0.102 | 2.40 | 2.80 |
| J | 0.018 | 0.024 | 0.46 | 0.61 |
| K | 0.500 | --- | 12.70 | --- |
| N | 0.080 | 0.105 | 2.04 | 2.66 |
| P | --- | 0.100 | --- | 2.54 |
| R | 0.135 | --- | 3.43 | --- |
| V | 0.135 | --- | 3.43 | --- |

STYLES ON PAGE 2

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[^0]
## TO-92 (TO-226) 1 WATT

CASE 29-10 ISSUE A

| STYLE 1: |  |
| ---: | :--- |
| PIN 1. | EMITTER |
| 2. | BASE |
| 3. | COLLECTOR |
| STYLE 6: |  |
| PIN 1. | GATE |
| 2. | SOURCE \& SUBSTRATE |
| 3. | DRAIN |
| STYLE 11: |  |
| PIN 1. | ANODE |
| 2. | CATHODE \& ANODE |
| 3. | CATHODE |
| STYLE 16: |  |
| PIN 1. | ANODE |
| 2. | GATE |
| 3. | CATHODE |
| STYLE 21: |  |
| PIN 1. | COLLECTOR |
| 2. | EMITTER |
| 3. | BASE |
| STYLE 26: |  |
| PIN 1. | VCC |
| 2. | GROUND 2 |
| 3. | OUTPUT |
| STYLE 31: |  |
| PIN 1. | GATE |
| 2. | DRAIN |
| 3. | SOURCE |


| STYLE 2: |  |
| ---: | :--- |
| PIN 1. | BASE |
| 2. | EMITTER |
| 3. | COLLECTOR |
| STYLE 7: |  |
| PIN 1. | SOURCE |
| 2. | DRAIN |
| 3. | GATE |
| STYLE 12: |  |
| PIN 1. | MAIN TERMINAL 1 |
| 2. | GATE |
| 3. | MAIN TERMINAL 2 |
| STYLE 17: |  |
| PIN 1. | COLLECTOR |
| 2. | BASE |
| 3. | EMITTER |
| STYLE 22: |  |
| PIN 1. | SOURCE |
| 2. | GATE |
| 3. | DRAIN |
| STYLE 27: |  |
| PIN 1. | MT |
| 2. | SUBSTRATE |
| 3. | MT |
| STYLE 32: |  |
| PIN 1. | BASE |
| 2. | COLLECTOR |
| 3. | EMITTER |


| STYLE 3: |  |
| ---: | :--- |
| PIN 1. | ANODE |
| 2. | ANODE |
| 3. | CATHODE |
| STYLE 8: |  |
| PIN 1. | DRAIN |
| 2. | GATE |
| 3. | SOURCE \& SUBSTRATE |
| STYLE 13: |  |
| PIN 1. | ANODE 1 |
| 2. | GATE |
| 3. | CATHODE 2 |
| STYLE 18: |  |
| PIN 1. | ANODE |
| 2. | CATHODE |
| 3. | NOT CONNECTED |
| STYLE 23: |  |
| PIN 1. | GATE |
| 2. | SOURCE |
| 3. | DRAIN |
| STYLE 28: |  |
| PIN 1. | CATHODE |
| 2. | ANODE |
| 3. | GATE |
| STYLE 33: |  |
| PIN 1. | RETURN |
| 2. | INPUT |
| 3. | OUTPUT |


| STYLE 4: PIN 1. | CATHODE | STYLE 5: PIN 1. | DRAIN |
| :---: | :---: | :---: | :---: |
| 2. | CATHODE | 2. | SOURCE |
| 3. | ANODE | 3. | GATE |
| STYLE 9: |  | STYLE 10: |  |
| PIN 1. | BASE 1 | PIN 1. | CATHODE |
| 2. | EMITTER | 2. | GATE |
| 3. | BASE 2 | 3. | ANODE |
| STYLE 14: |  | STYLE 15: |  |
| PIN 1. | EMITTER | PIN 1. | ANODE 1 |
| 2. | COLLECTOR | 2. | CATHODE |
| 3. | BASE | 3. | ANODE 2 |
| STYLE 19: |  | STYLE 20: |  |
| PIN 1. | GATE | PIN 1. | NOT CONNECTED |
| 2. | ANODE | 2. | CATHODE |
| 3. | CATHODE | 3. | ANODE |
| STYLE 24: |  | STYLE 25: |  |
| PIN 1. | EMITTER | PIN 1. | MT 1 |
| 2. | COLLECTOR/ANODE | 2. | GATE |
| 3. | CATHODE | 3. | MT 2 |
| STYLE 29: |  | STYLE 30: |  |
| PIN 1. | NOT CONNECTED | PIN 1. | DRAIN |
| 2. | ANODE | 2. | GATE |
| 3. | CATHODE | 3. | SOURCE |
| STYLE 34: |  | STYLE 35: |  |
| PIN 1. | INPUT | PIN 1. | GATE |
| 2. | GROUND | 2. | COLLECTOR |
| 3. | LOGIC | 3. | EMITTER |


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